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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/653,281	08/31/2000	Kevin L. Beaman	M4065.0278/P27899-0818 4745		
7590 11/01/2004			EXAMINER		
Thomas J D'Amico			BOOTH, RICHARD A		
Dickstein Shar	oiro Morin & Oshinsky				
2101 L Street NW			ART UNIT	PAPER NUMBER	
Washington, I	OC 20037-1526	2812			

DATE MAILED: 11/01/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application	No.	Applicant(s)				
Office Action Summary		09/653,281		BEAMAN ET AL.				
		Examiner		Art Unit				
		Richard A. B		2812	_			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply								
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).								
Status								
1)⊠	Responsive to communication(s) filed on 27 S	September 20	<u>04</u> .					
2a) <u></u> □	·							
3)	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is							
	closed in accordance with the practice under the	Ex parte Qua	<i>yle</i> , 1935 C.D. 11, 45	3 O.G. 213.				
Disposit	ion of Claims							
4) 🖂	Claim(s) 1-3,6-14,16,18,21-29,31 and 35-45 is	s/are pending	in the application.					
	4a) Of the above claim(s) is/are withdra	wn from con	sideration.					
	Claim(s) is/are allowed.							
•	6)⊠ Claim(s) <u>1-3,6-14,16,18,21-29,31 and 35-45</u> is/are rejected.							
· —	7) Claim(s) is/are objected to.							
8)∐	Claim(s) are subject to restriction and/o	or election rec	quirement.					
Applicat	ion Papers							
,	The specification is objected to by the Examine		_					
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.								
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.								
11)[_]	The oath of declaration is objected to by the E	xanınıer. Nu	e the attached Office	Action of form F 10-132.				
Priority (	under 35 U.S.C. § 119							
12)	Acknowledgment is made of a claim for foreign	n priority und	er 35 U.S.C. § 119(a)	-(d) or (f).				
a)	☐ All b)☐ Some * c)☐ None of:							
	1. Certified copies of the priority documen			a.a. Alla				
	2. Certified copies of the priority documen							
	3. Copies of the certified copies of the price application from the International Burea			iu iii iiiis ivalionai Stage				
* 9	See the attached detailed Office action for a lis	•		ed.				
·	soo the ditablica dotalisa cilico dotali ioi a lie							
Attachment(s)								
	ce of References Cited (PTO-892)		4) Interview Summary Paper No(s)/Mail D					
3) Infor	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08 er No(s)/Mail Date	3)		Patent Application (PTO-152)				

#### **DETAILED ACTION**

#### Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 9/27/04 has been entered.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-3, 6-16, 18, 21-31, and 34-45 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wang et al., U.S. Patent 6,376,309 in view of Hoff et al., "Atomic Oxygen and the thermal oxidation of silicon" or Ruzyllo et al., "Evaluation of Thin Oxides Grown by the Atomic Oxygen Afterglow Method".

Wang et al. shows the invention as claimed including forming a tunnel oxide 404 on a substrate 402; forming a first conductor 406 over the tunnel oxide 404; forming an insulating layer 410 over the first conductor layer, the insulating layer comprising a first oxide layer over the first conductor layer, a nitride layer over the first oxide layer, and a second oxide layer over the nitride layer, wherein the second oxide layer is formed by

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oxidizing said nitride layer to a thickness of fifty angstroms (see column 3, lines 39-54); forming a second conductor layer 412 over the insulating layer; etching at least the first conductor layer, the second conductor layer, and the insulating layer, thereby defining at least one stacked structure (see Figure 3).

Note, the hydrogen and oxygen present when forming the second oxide layer will react to form steam.

Wang et al. fails to show forming the second oxide layer using an oxidizing ambient in atomic oxygen to form the oxide layer with a thickness of 60% of a targeted thickness and at various temperatures and times.

Both Hoff et al., "Atomic Oxygen and the thermal oxidation of silicon" and Ruzyllo et al., "Evaluation of Thin Oxides Grown by the Atomic Oxygen Afterglow Method" disclose forming an oxide layer in a microwave environment using an oxidizing method with atomic oxygen (see abstracts of both methods). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Wang et al. so as to form the second oxide layer using the process taught by Hoff et al. or Ruzyllo et al. because both of these processes allow for oxide growth at low temperatures with high breakdown values.

With respect to the particular time and temperature of the oxidation, it would have been obvious to determine through routine experimentation the optimum time and temperature to conduct the oxidation process based upon a variety of factors including the desired thermal budget and would not lend patentability to the instant application absent the showing of unexpected results.

## Response to Arguments

Applicant's arguments filed 9/27/04 have been fully considered but they are not persuasive. Regarding applicant's argument that the references fail to show an ISSG process, one cannot show nonobviousness by attacking references individually where the rejections are based on combinations of references (Wang shows this process). See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981); *In re Merck & Co.*, 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986).

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is (571) 272-1668. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

Richard A. Booth Primary Examiner Art Unit 2812

October 29, 2004